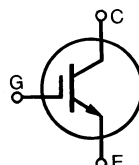


HiPerFAST™ IGBT Lightspeed™ Series

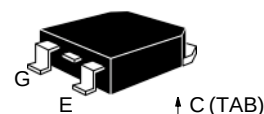
IXGH 32N60C
IXGT 32N60C

$V_{CES} = 600 \text{ V}$
 $I_{C25} = 60 \text{ A}$
 $V_{CE(sat)typ} = 2.1 \text{ V}$
 $t_{fi typ} = 55 \text{ ns}$

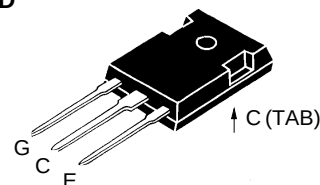


Symbol	Test Conditions	Maximum Ratings	
V_{CES}	$T_J = 25^\circ\text{C to } 150^\circ\text{C}$	600	V
V_{CGR}	$T_J = 25^\circ\text{C to } 150^\circ\text{C}; R_{GE} = 1 \text{ M}\Omega$	600	V
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C25}	$T_C = 25^\circ\text{C}$	60	A
I_{C110}	$T_C = 110^\circ\text{C}$	32	A
I_{CM}	$T_C = 25^\circ\text{C}, 1 \text{ ms}$	120	A
SSOA (RBSOA)	$V_{GE} = 15 \text{ V}, T_{VJ} = 125^\circ\text{C}, R_G = 10 \Omega$ Clamped inductive load, $L = 100 \mu\text{H}$	$I_{CM} = 64$ @ $0.8 V_{CES}$	A
P_C	$T_C = 25^\circ\text{C}$	200	W
T_J		-55 ... +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-55 ... +150	$^\circ\text{C}$
Maximum lead temperature for soldering 1.6 mm (0.062 in.) from case for 10 s		300	$^\circ\text{C}$
M_d	Mounting torque (M3)	1.13/10 Nm/lb.in.	
Weight	TO-247 AD	6	g
	TO-268	4	g

**TO-268
(IXGT)**



**TO-247 AD
(IXGH)**



G = Gate, C = Collector,
E = Emitter, TAB = Collector

Features

- International standard packages JEDEC TO-247 and surface mountable TO-268
- High current handling capability
- Latest generation HDMOS™ process
- MOS Gate turn-on - drive simplicity

Applications

- PFC circuits
- Uninterruptible power supplies (UPS)
- Switched-mode and resonant-mode power supplies
- AC motor speed control
- DC servo and robot drives
- DC choppers

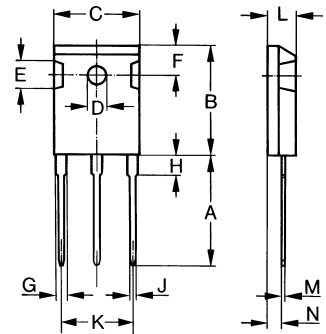
Advantages

- High power density
- Very fast switching speeds for high frequency applications

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
BV_{CES}	$I_C = 250 \mu\text{A}, V_{GE} = 0 \text{ V}$	600		V
$V_{GE(th)}$	$I_C = 250 \mu\text{A}, V_{CE} = V_{GE}$	2.5		5 V
I_{CES}	$V_{CE} = 0.8 \cdot V_{CES}$ $V_{GE} = 0 \text{ V}$			$200 \mu\text{A}$ 1 mA
I_{GES}	$V_{CE} = 0 \text{ V}, V_{GE} = \pm 20 \text{ V}$			$\pm 100 \text{ nA}$
$V_{CE(sat)}$	$I_C = I_{C110}, V_{GE} = 15 \text{ V}$	2.1	2.5	V

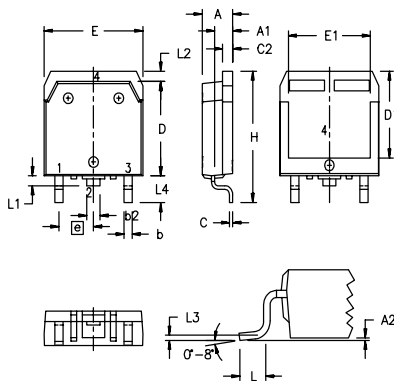
Symbol	Test Conditions	Characteristic Values ($T_j = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
g_{fs}	$I_C = I_{C110}$; $V_{CE} = 10\text{ V}$, Pulse test, $t \leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$		25	S
C_{ies}	$V_{CE} = 25\text{ V}$, $V_{GE} = 0\text{ V}$, $f = 1\text{ MHz}$		2700	pF
C_{oes}			190	pF
C_{res}			50	pF
Q_g	$I_C = I_{C110}$, $V_{GE} = 15\text{ V}$, $V_{CE} = 0.5 V_{CES}$		110	nC
Q_{ge}			22	nC
Q_{gc}			40	nC
$t_{d(on)}$	Inductive load, $T_j = 25^\circ\text{C}$ $I_C = I_{C110}$, $V_{GE} = 15\text{ V}$, $L = 100\text{ }\mu\text{H}$, $V_{CE} = 0.8 V_{CES}$, $R_G = R_{off} = 4.7\text{ }\Omega$ Remarks: Switching times may increase for $V_{CE}(\text{Clamp}) > 0.8 \cdot V_{CES}$, higher T_j or increased R_G		25	ns
t_{ri}			20	ns
$t_{d(off)}$			85	ns
t_{fi}			55	ns
E_{off}			0.32	mJ
$t_{d(on)}$	Inductive load, $T_j = 150^\circ\text{C}$ $I_C = I_{C110}$, $V_{GE} = 15\text{ V}$, $L = 100\text{ }\mu\text{H}$, $V_{CE} = 0.8 V_{CES}$, $R_G = R_{off} = 4.7\text{ }\Omega$ Remarks: Switching times may increase for $V_{CE}(\text{Clamp}) > 0.8 \cdot V_{CES}$, higher T_j or increased R_G		25	ns
t_{ri}			25	ns
E_{on}			0.30	mJ
$t_{d(off)}$			110	170 ns
t_{fi}			105	160 ns
E_{off}			0.85	1.25 mJ
R_{thJC}				0.62 K/W
R_{thCK}	(IXGH32N60C)		0.25	K/W

TO-247 AD (IXGH) Outline



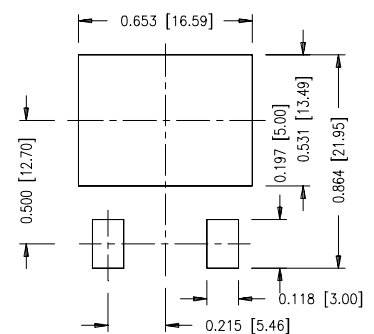
Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	19.81	20.32	0.780	0.800
B	20.80	21.46	0.819	0.845
C	15.75	16.26	0.610	0.640
D	3.55	3.65	0.140	0.144
E	4.32	5.49	0.170	0.216
F	5.4	6.2	0.212	0.244
G	1.65	2.13	0.065	0.084
H	-	4.5	-	0.177
J	1.0	1.4	0.040	0.055
K	10.8	11.0	0.426	0.433
L	4.7	5.3	0.185	0.209
M	0.4	0.8	0.016	0.031
N	1.5	2.49	0.087	0.102

TO-268AA (D³ PAK)



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.9	5.1	.193	.201
A ₁	2.7	2.9	.106	.114
A ₂	.02	.25	.001	.010
b	1.15	1.45	.045	.057
b ₂	1.9	2.1	.75	.83
C	.4	.65	.016	.026
D	13.80	14.00	.543	.551
E	15.85	16.05	.624	.632
E ₁	13.3	13.6	.524	.535
e	5.45 BSC		.215 BSC	
H	18.70	19.10	.736	.752
L	2.40	2.70	.094	.106
L ₁	1.20	1.40	.047	.055
L ₂	1.00	1.15	.039	.045
L ₃	0.25 BSC		.010 BSC	
L ₄	3.80	4.10	.150	.161

Min. Recommended Footprint



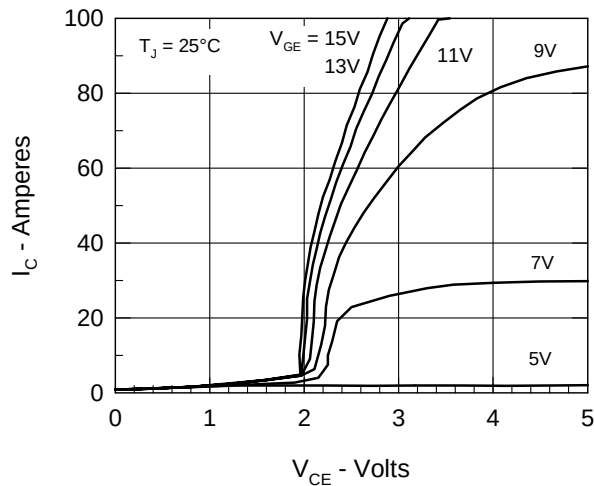


Fig. 1. Output Characteristics

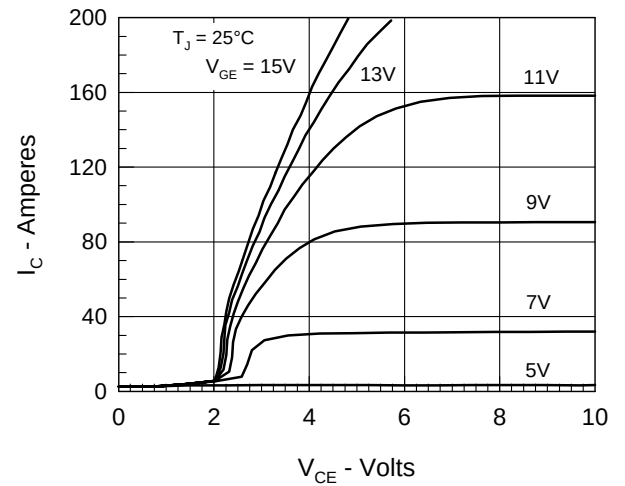


Fig. 2. Extended Output Characteristics

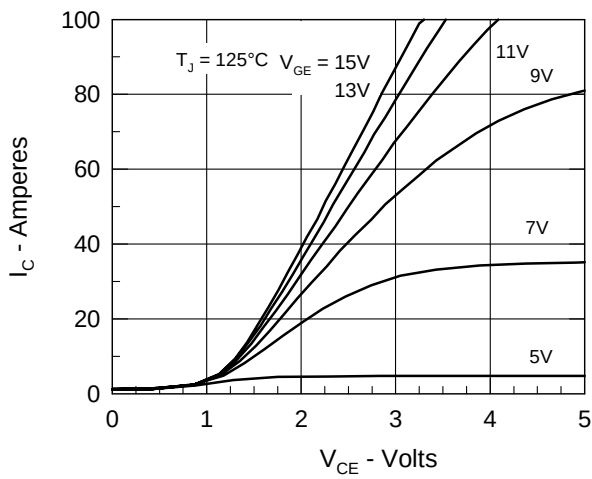


Fig. 3. High Temperature Output Characteristics

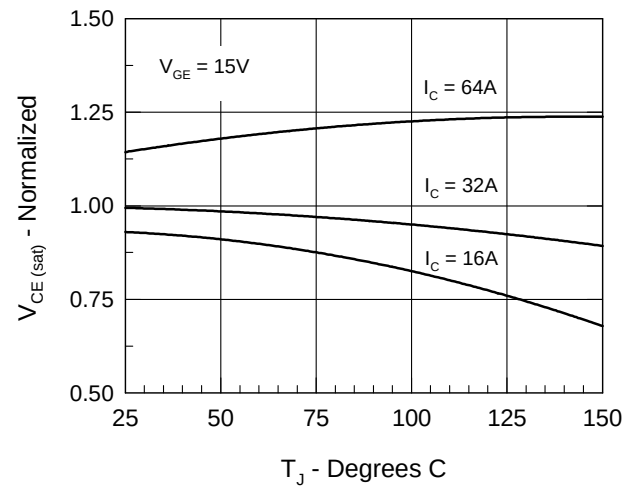


Fig. 4. Temperature Dependence of $V_{CE(sat)}$

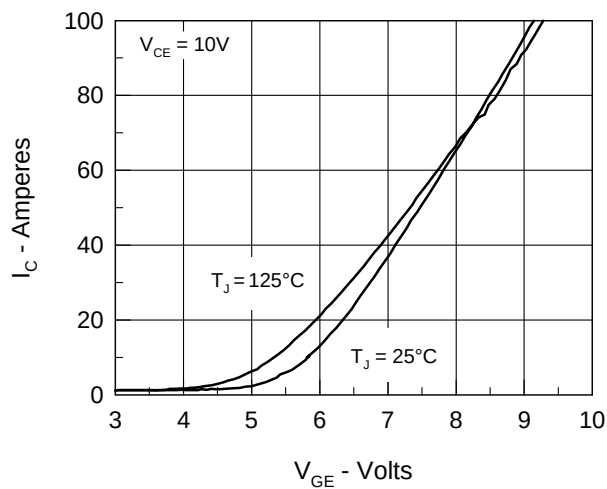


Fig. 5. Admittance Curves

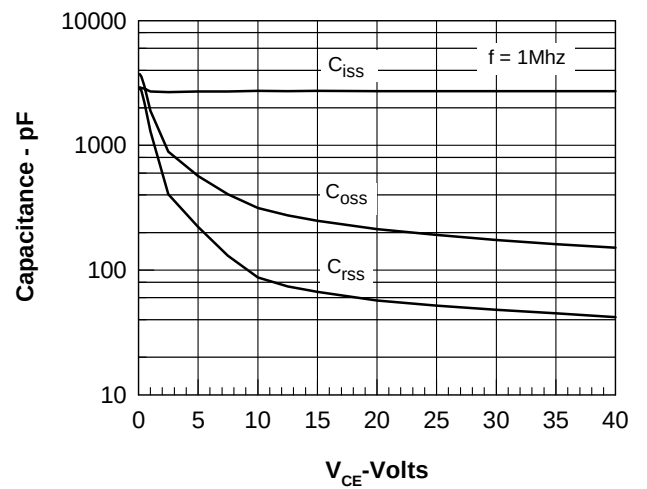


Fig. 6. Capacitance Curves

